

**2N3436
2N3437
2N3438**

**CASE 22-03, STYLE 4
TO-18 (TO-206AA)**

**JFET
LOW-FREQUENCY**

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	50	Vdc
Gate-Source Voltage	V_{GS}	50	Vdc
Gate Current	I_G	10	mA
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 1.7	mW mW/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +175	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage ($I_G = 1.0 \mu\text{A}$)	$V_{(BR)GSS}$	50	—	Vdc
Gate Reverse Current ($V_{GS} = -30 \text{ V}$)	I_{GSS}	—	0.5	nA
Gate Source Cutoff Voltage ($V_{DS} = 20 \text{ V}$, $I_D = 1.0 \mu\text{A}$)	$V_{GS(off)}$	—	10.0 5.0 2.5	Vdc
Gate Source Voltage ($V_{DS} = 20 \text{ V}$, $I_D = 1.0 \mu\text{A}$)	V_{GS}	—	9.8 4.8 2.3	Vdc

ON CHARACTERISTICS

Zero-Gate-Voltage Drain Current ($V_{DS} = 20 \text{ V}$)	I_{DSS}^*	3.0 0.8 0.2	15 4.0 1.0	mA
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SMALL-SIGNAL CHARACTERISTICS

Forward Transfer Admittance ($V_{DS} = 20 \text{ V}$, $f = 1.0 \text{ kHz}$)	$ Y_{fs} $	2500 1500 800	10000 6000 4500	μmhos
Output Admittance ($V_{DS} = 30 \text{ V}$, $f = 1.0 \text{ kHz}$)	$ Y_{os} $	— — —	35 20 5	μmhos
Input Capacitance ($V_{DS} = 10 \text{ V}$) ($V_{DS} = 6.0 \text{ V}$) ($V_{DS} = 4.0 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_{iss}	—	18	pF

FUNCTIONAL CHARACTERISTICS

Noise Figure ($V_{DS} = 10 \text{ V}$, $R_G = 1.0 \text{ m}\Omega$, $f = 1.0 \text{ kHz}$)	NF	—	2.0	dB
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*Pulse Width $\leq 630 \text{ msec}$, Duty Cycle $\leq 10\%$.